

STS4300-VB Datasheet

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$		Q _g (Typ.)			
30	0.030 at V _{GS} = 10 V	6.5	4.5 nC			
	0.033 at V _{GS} = 4.5 V	6.0	4.5 nC			

FEATURES

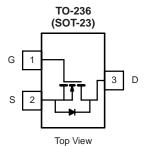
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

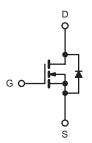


ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

DC/DC Converter





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V_{DS}	30	V		
Gate-Source Voltage		V_{GS}	± 20			
	T _C = 25 °C		6.5 ^a			
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	I _D	6.0			
Continuous Brain Carron (1) = 100 C)	T _A = 25 °C		5.3			
	T _A = 70 °C		5.0	Α		
Pulsed Drain Current		I _{DM}	25	j		
	T _C = 25 °C		1.4			
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	0.9 ^{b, c}			
	T _C = 25 °C		1.7			
Maximum Power Dissipation	$T_C = 70 ^{\circ}C$	P _D	1.1	w		
Waximum Tower Dissipation	$T_A = 25 ^{\circ}C$	l 'b	1.1 ^{b, c}			
	T _A = 70 °C		0.7 ^{b, c}			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Tempera	ture) ^{d, e}		260			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R_{thJA}	90	115	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	60	75	0/11	

Notes:

- a. Package limited
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under steady state conditions is 130 $^{\circ}\text{C/W}.$



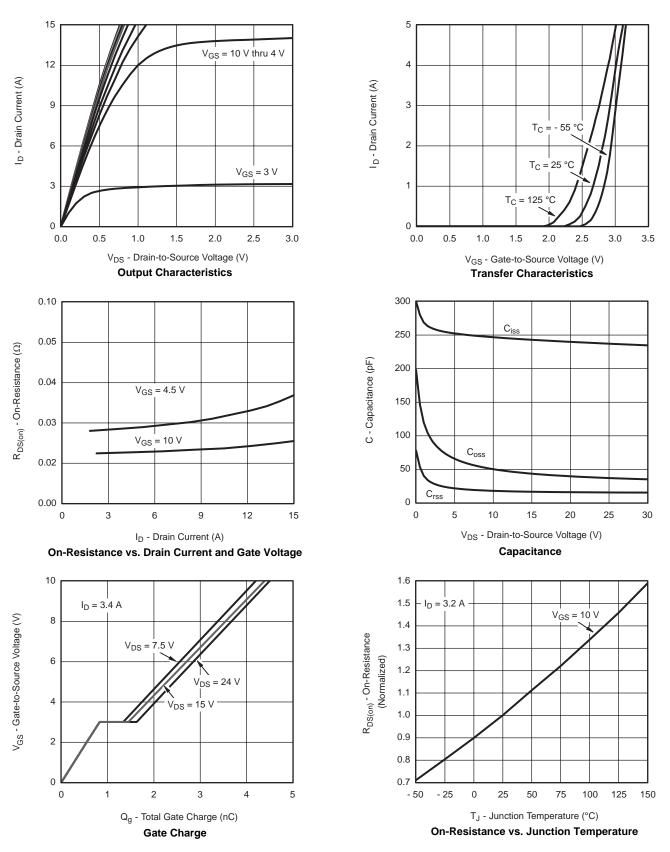
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						•
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$	30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		31		mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 5		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.7	1.1	2.0	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zana Oata Waltana Busin Oamani		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α
	_	$V_{GS} = 10 \text{ V}, I_D = 3.2 \text{ A}$		0.030		Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 2.8 \text{ A}$		0.033		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 4.8 A		11		S
Dynamic ^b					l .	
Input Capacitance	C _{iss}			335		pF
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		45		
Reverse Transfer Capacitance	C _{rss}			17		
Total Cata Charge	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 3.4 \text{ A}$		4.5	6.7	nC
Total Gate Charge				2.1	3.2	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 3.4 \text{ A}$		0.85		
Gate-Drain Charge	Q _{gd}			0.65		
Gate Resistance	R _g	f = 1 MHz	0.8	4.4	8.8	Ω
Turn-On Delay Time	t _{d(on)}			12	20	ns
Rise Time	t _r	V_{DD} = 15 V, R_L = 5.6 Ω		50	75	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 2.7 A, V_{GEN} = 4.5 V, R_g = 1 Ω		12	20	
Fall Time	t _f			22	35	
Turn-On Delay Time	t _{d(on)}			5	10	
Rise Time	t _r	V_{DD} = 15 V, R_L = 5.6 Ω		12	20	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 2.7 A, V_{GEN} = 10 V, R_g = 1 Ω		10	15	
Fall Time	t _f			5	10	
Drain-Source Body Diode Characteristi	cs					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			1.4	Δ
Pulse Diode Forward Current	I _{SM}				15	A
Body Diode Voltage	V _{SD}	I _S = 2.7 A, V _{GS} = 0 V		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			10	20	ns
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 2.7 A, dI/dt = 100 A/μs, T _J = 25 °C		5	10	nC
Reverse Recovery Fall Time	t _a	$I_F = 2.7$ A, $U_1/U_1 = 100 \text{ A/}\mu\text{s}$, $I_J = 25 ^{\circ}\text{C}$		6		
Reverse Recovery Rise Time	t _b			4		ns

Notes:

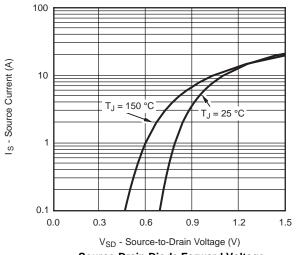
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

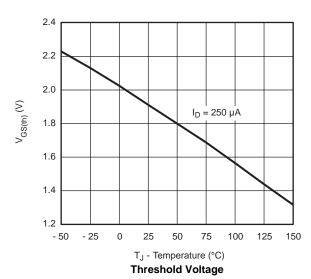


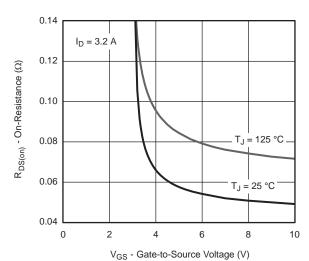




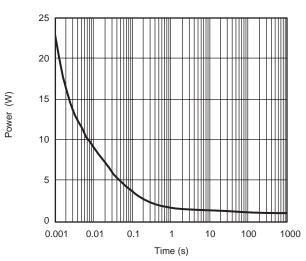


Source-Drain Diode Forward Voltage

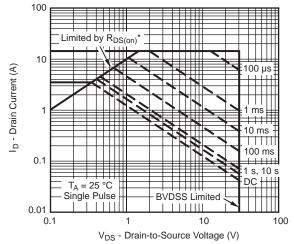




On-Resistance vs. Gate-to-Source Voltage



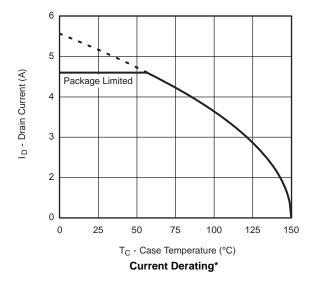
Single Pulse Power

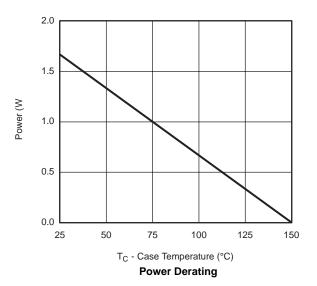


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

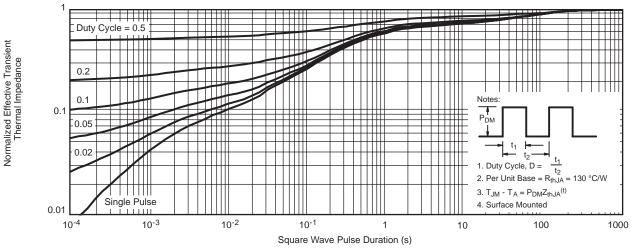






^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





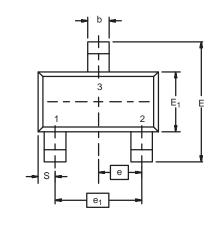
Normalized Thermal Transient Impedance, Junction-to-Ambient

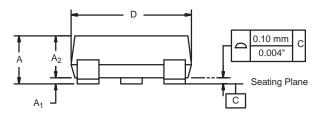


Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD







Dim -	MILLIM	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01				

DWG: 5479



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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